

**Silicon NPN Power Transistors**

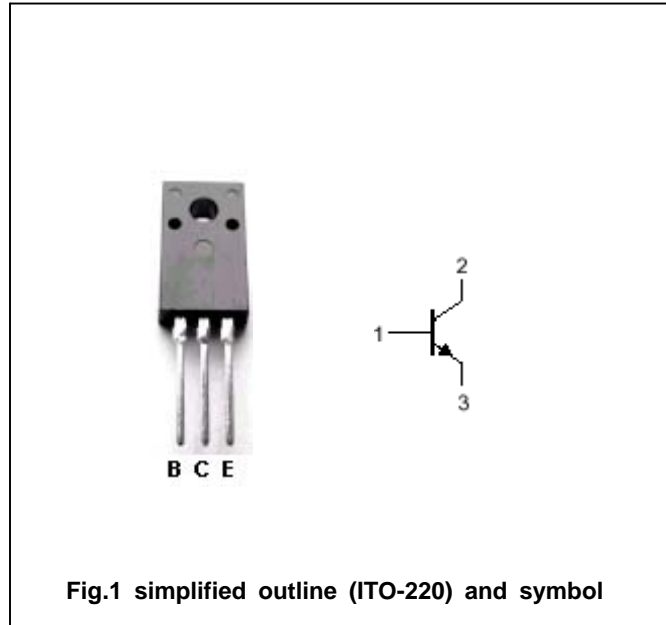
**2SC4833**

**DESCRIPTION**

- With ITO-220 package
- Switching power transistor

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



**Absolute maximum ratings(Ta=25 )**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	500	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	400	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	7	V
I <sub>C</sub>	Collector current		5	A
I <sub>CM</sub>	Collector current-Peak		10	A
I <sub>B</sub>	Base current		2	A
I <sub>BM</sub>	Base current-Peak		4	A
P <sub>T</sub>	Total power dissipation	T <sub>C</sub> =25	35	W
T <sub>j</sub>	Junction temperature		150	
T <sub>stg</sub>	Storage temperature		-55~150	
V <sub>dis</sub>	Dielectric strength	Terminals to case,AC1 minute	2	kV
TOR	Mounting torque	(Recommended torque:0.3N·m)	0.5	N·m

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-C</sub>	Thermal resistance junction to case	3.57	/W

## Silicon NPN Power Transistors

## 2SC4833

## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =0.1A ; I <sub>B</sub> =0	400			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =2.5A; I <sub>B</sub> =0.5A			1.0	V
V <sub>BEsat</sub>	Emitter-base saturation voltage	I <sub>C</sub> =2.5A; I <sub>B</sub> =0.5A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	At rated volatge			0.1	mA
I <sub>CEO</sub>	Collector cut-off current					
I <sub>EBO</sub>	Emitter cut-off current	At rated volatge			0.1	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =2.5A ; V <sub>CE</sub> =2V	10		25	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =1mA ; V <sub>CE</sub> =2V	10			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.5A ; V <sub>CE</sub> =10V		13		MHz
t <sub>on</sub>	Turn-on time	I <sub>C</sub> =2.5A; I <sub>B1</sub> =0.5A I <sub>B2</sub> =1A , R <sub>L</sub> =60 V <sub>BB2</sub> =4V			0.3	μs
t <sub>s</sub>	Storage time				1.3	μs
t <sub>f</sub>	Fall time				0.1	μs

Silicon NPN Power Transistors

2SC4833

PACKAGE OUTLINE

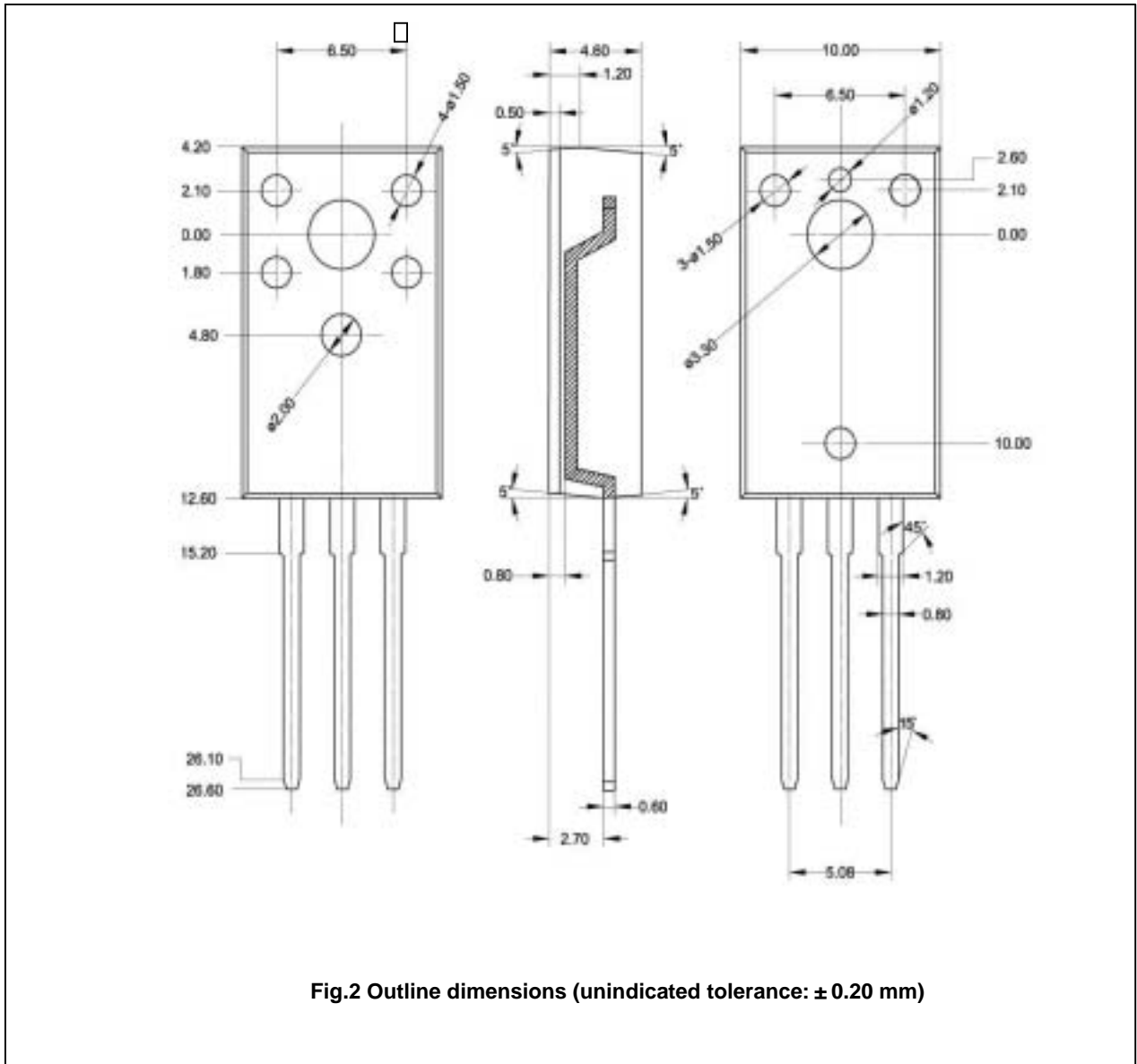


Fig.2 Outline dimensions (unindicated tolerance:  $\pm 0.20$  mm)